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(54) SUPERJUNCTION SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING SAME

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(57) **ABSTRACT**

Disclosed are a superjunction semiconductor device and a method of manufacturing the same. More particularly, a superjunction semiconductor device and a method of manufacturing the same include an additional structure that enables smooth current flow in a transition region and/or a ring region of the device, where the current concentrates locally during turn-on/turn-off operations of the device due to insufficient current paths compared to the cell region of the device, thereby improving reverse recovery characteristics and preventing device destruction.